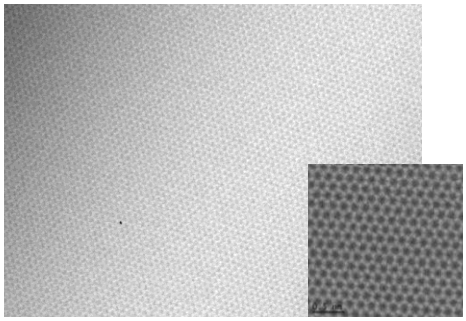
# CVD Graphene on Cu foil

## Ultra-Clean Graphene on SiO2/Si Wafer

50mm X 50mm, 1ea

| | |
|---|---|
| **Product Size** | Up to 90 x 90 ㎟ (Max) |
| **Film Morphology** | Continuous Monolayer (>95%) |
| **Sheet Resistance** | Av. < 250~400 Ω/sq |
| **Mobility** | >3500 $cm^2/Vs$ (Max. 17,000 $cm^2/Vs$) |
| **Transmittance** | >97% |
| **Substrate** | $SiO_2$(300nm)/Si wafer (Standard) |
| **Domain Size** | 10-20 ㎛ |

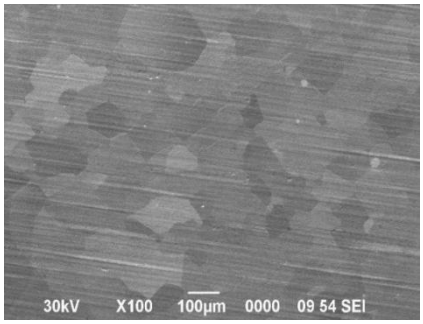
### High-Resolution TEM Images



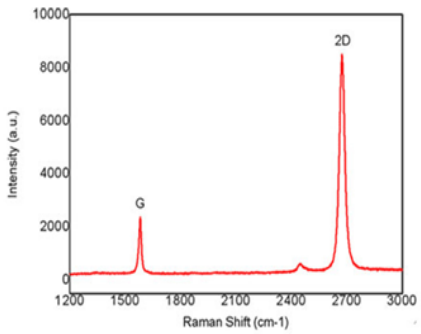
### Substrate specifications

| | |
|---|---|
| **Orientation** | <100> |
| **Thickness** | 525±25 ㎛ |
| **Oxide Thickness** | 300nm |
| **Type/Dopant** | P/Boron |
| **Resistivity** | Resistivity |

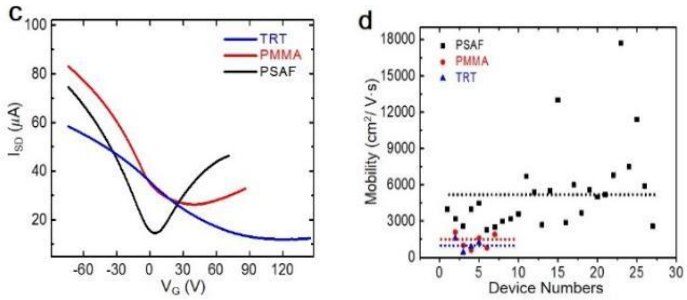
### SEM Image of Graphene on Cu



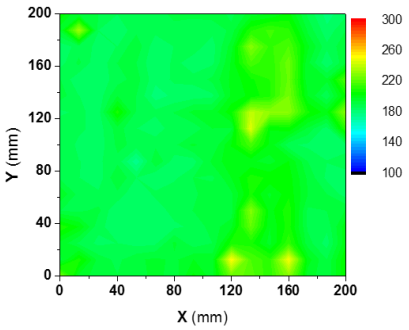

### Raman Spectrum



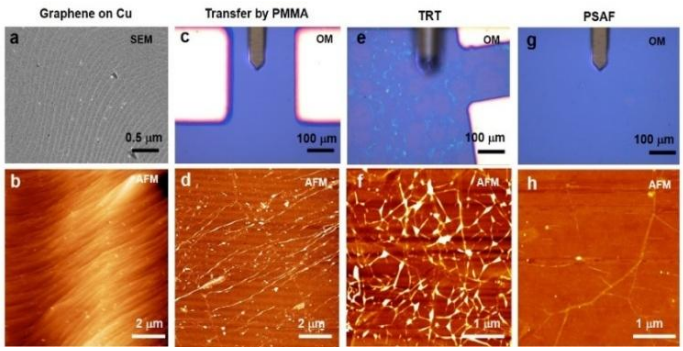
## Electrical Properties




## Sheet Resistance Uniformity




## Ultra-Clean Transfer by Pressure Sensitive Adhesive Films




## Reference

(1) S. Kim *et. al*. **Ultra-Clean Patterned Transfer of Single-Layer Graphene by Recyclable Pressure Sensitive Adhesive Films.** *Nano Lett.* (accepted).

(2) S. Bae*, H. Kim* *et al*. **Roll-to-roll production of 30 inch graphene films for transparent electrodes** *Nature Nanotech*. **5**, 574 (2010).